SG2M018120BJ

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2 N Channel Enhancement

Features

- High speed switching
- Very low switching losses
- Fully controllable dv/dt
- High blocking

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1 Maximum ratings

Table 2 Maximum rating (Tc = 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{GSOP}					

2 Electrical characteristics

2.1 Static characteristics

Table 4 Static characteristics (Tc = 25°C unless otherwise specified)

Q_{gs}	Gate source charge	-	34	-	nC	V_{DS} = 800V, V_{GS} = -4/+18V I_D = 64A	Fig.12
Q_{gd}	Gate drain charge	-	32	-			
Q_g	Gate charge	-	106	-			

2.3 Switching characteristics

Table 6 Dynamic characteristics(Tc = 25°C unless otherwise specified,the data comes from TO-247-4L)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
E_{on}	Turn on switching energy	-	740	-			

3 Electrical characteristic diagrams

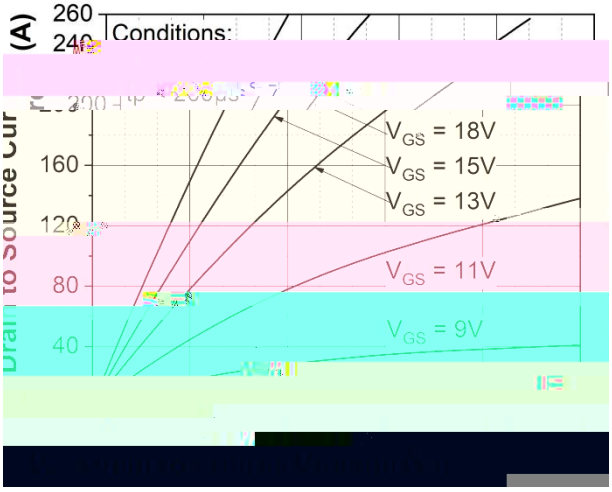


Figure 1. Output characteristics T_J = -55 ºC

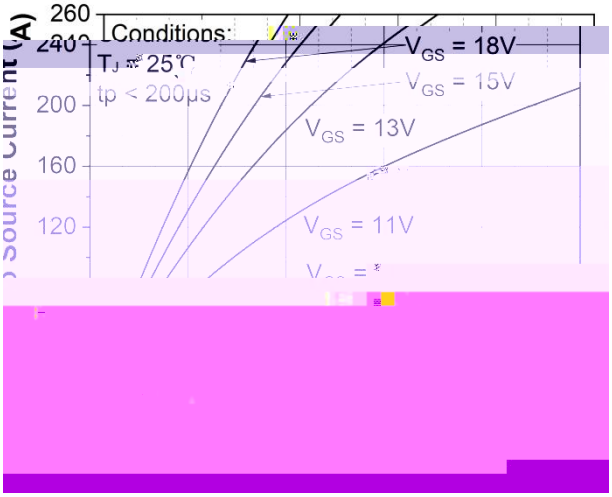


Figure 2. Output characteristics T_J = 25 ºC

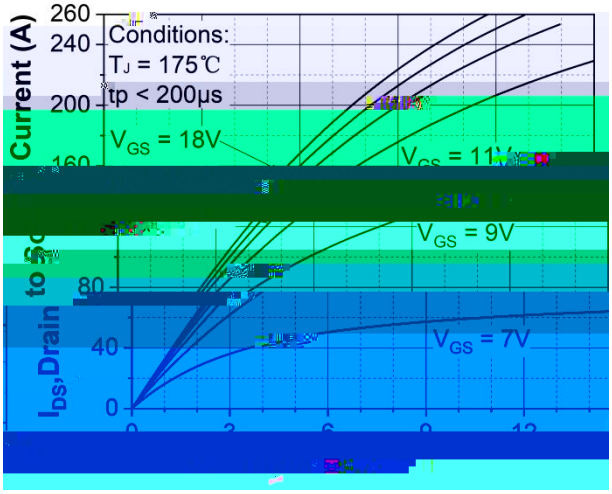


Figure 3. Output characteristics T_J = 175 ºC

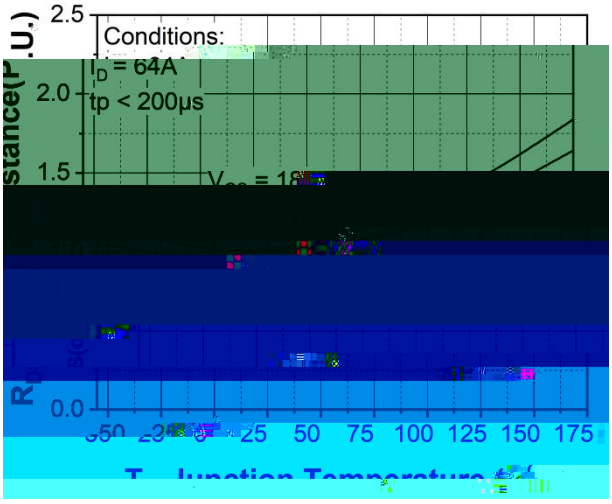


Figure 4. Normalized on-resistance vs. temperature

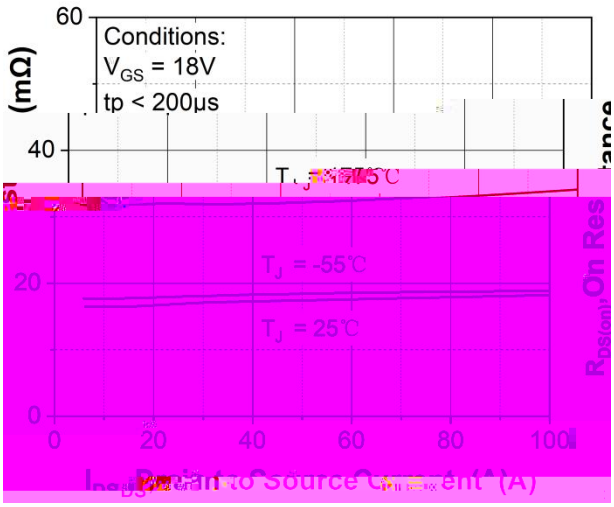


Figure 5. On-resistance vs. drain current for various temperatures

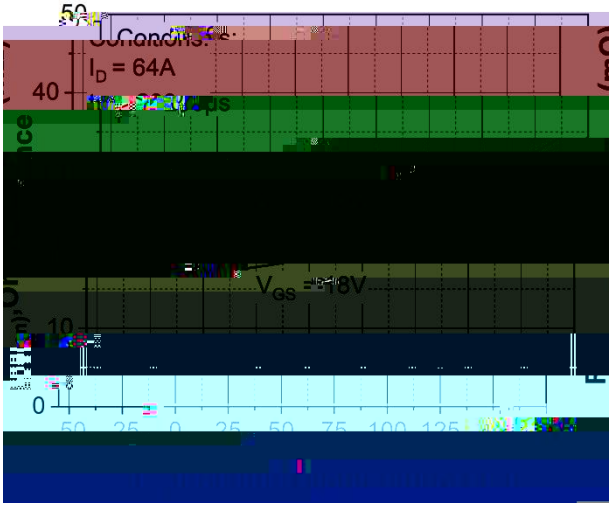


Figure 6. On-resistance vs. temperature for various gate voltages

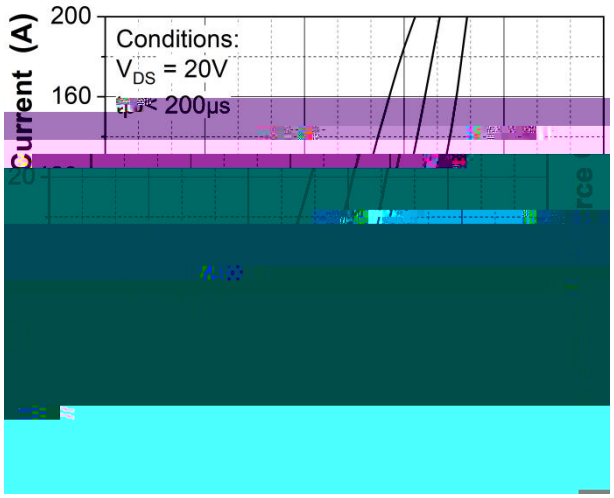


Figure 7. Transfer characteristic for various junction temperatures

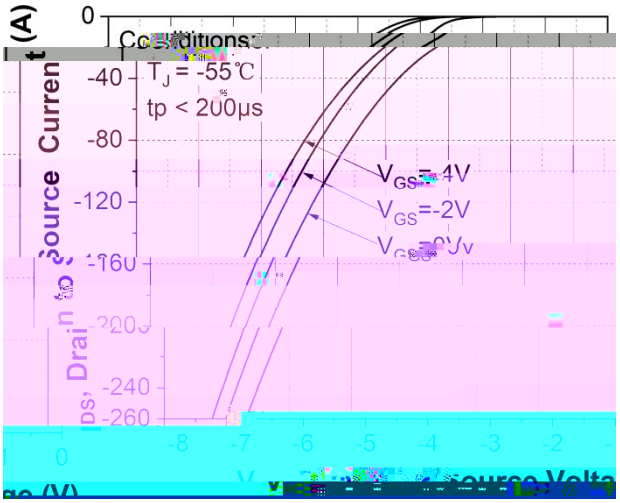


Figure 8. Body diode characteristic at T_J = -55 ºC

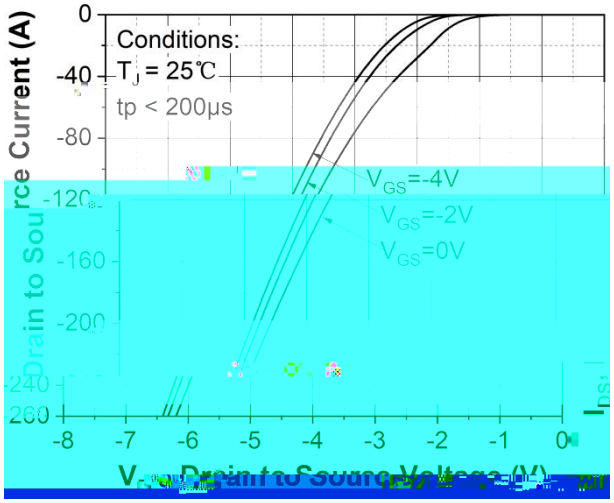


Figure 9. Body diode characteristic at T_J = 25 ºC

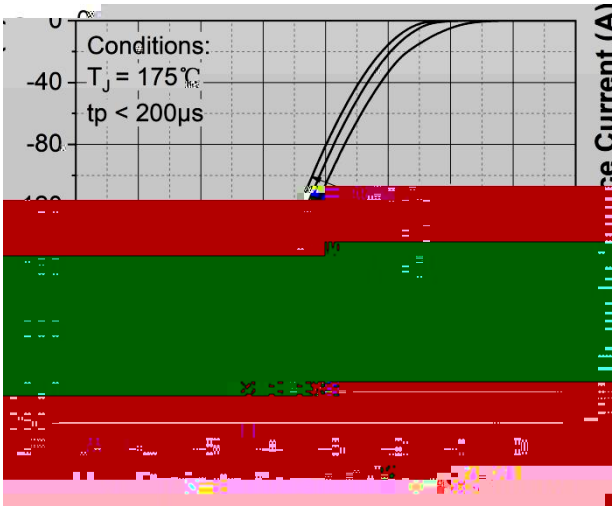


Figure 10. Body diode characteristic at T_J = 175ºC

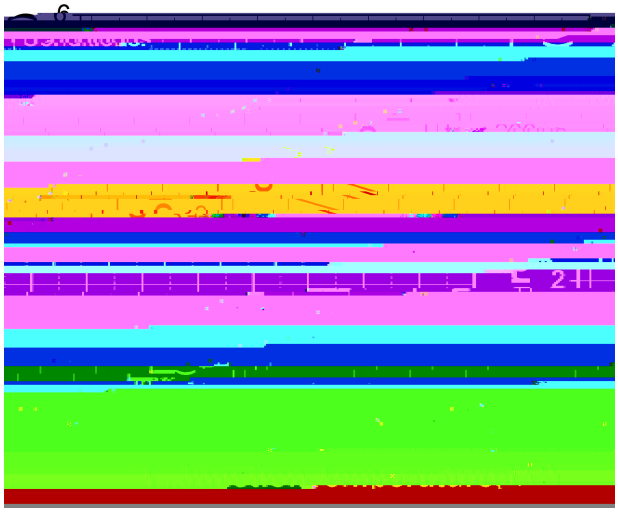


Figure 11. Threshold voltage vs. temperature

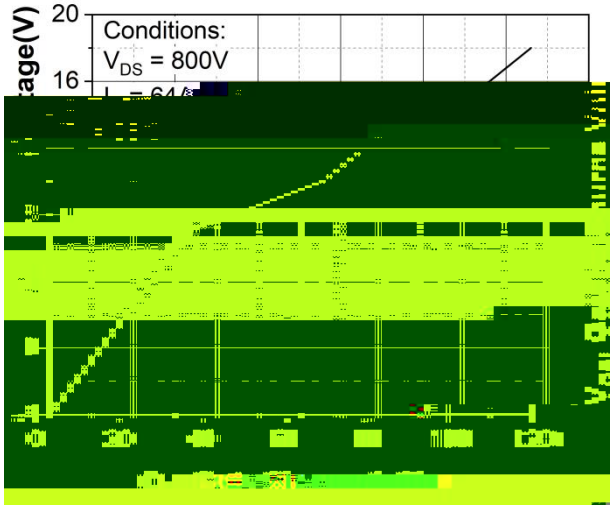


Figure 12. Gate charge characteristic

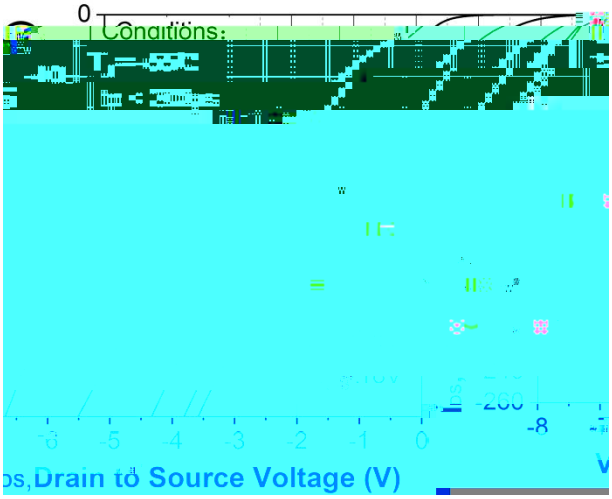


Figure 13. 3rd quadrant characteristic at T_J = -55 ºC

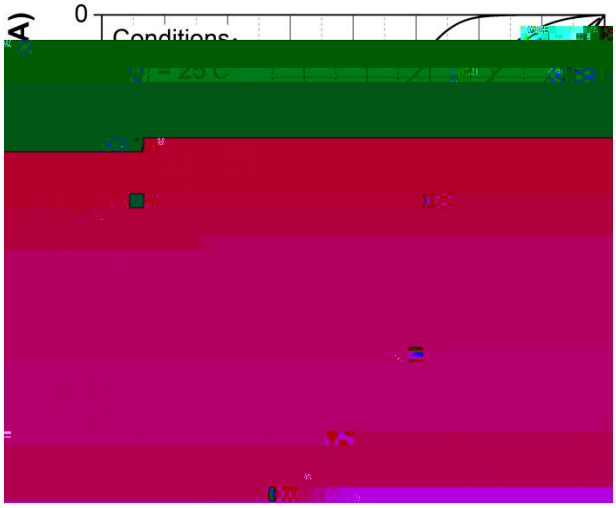


Figure 14. 3rd quadrant characteristic at T_J = 25 ºC

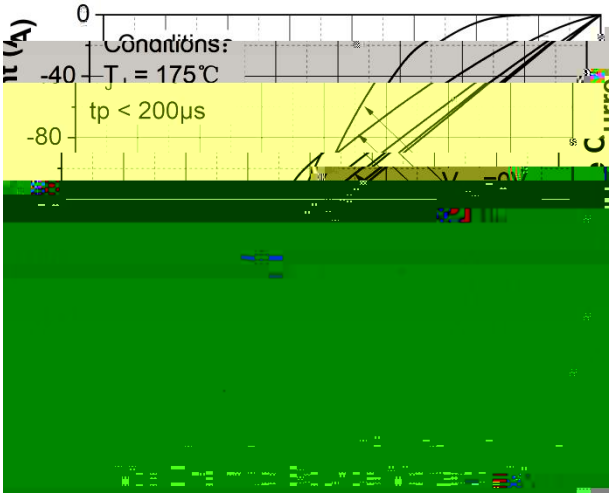


Figure 15. 3rd quadrant characteristic at T_J = 175 ºC

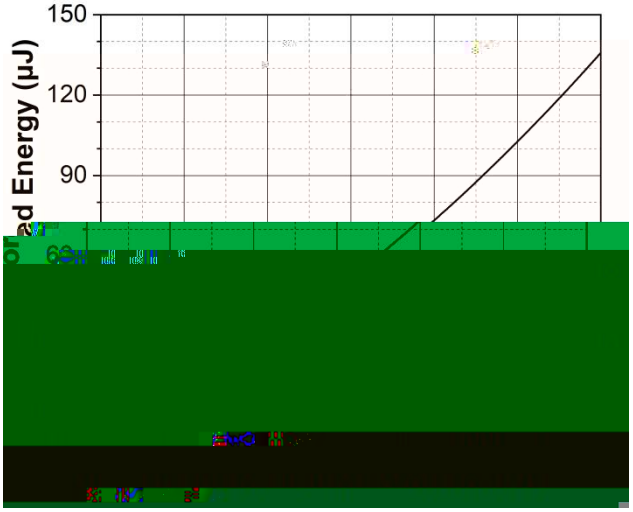


Figure 16. Output capacitor stored energy

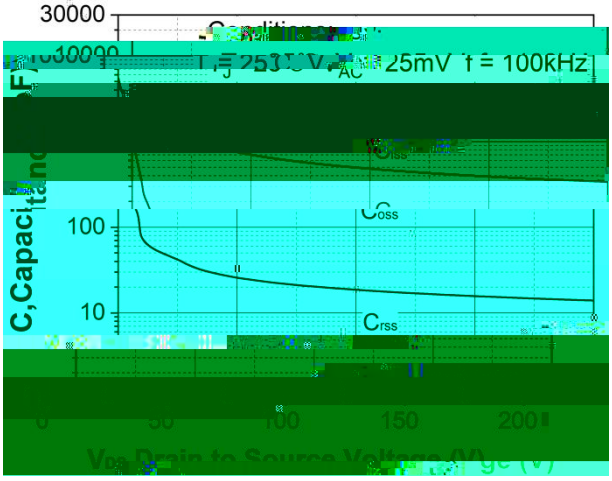


Figure 17. Capacitances vs. drain-source voltage (0 - 200V)

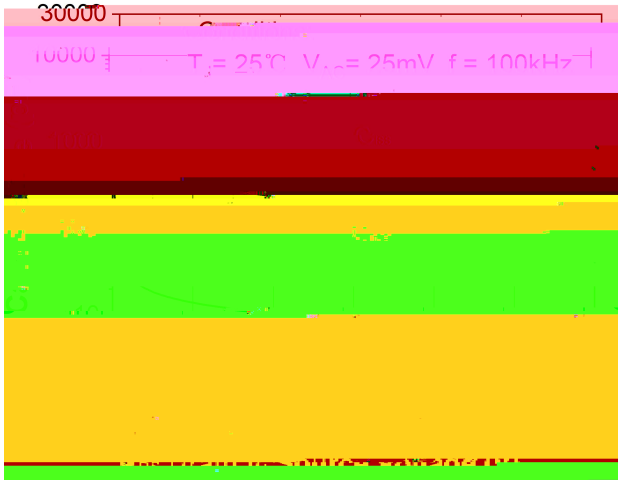


Figure 18. Capacitances vs. drain-source voltage (0 - 1200V)

4. Mechanical parameters

4.1 Dimensions and metallization

Parameter	Typical value	Unit	Metallization
Die size W x L	4.46*5.02	mm	
Gate pad size W x L	0.80*0.80	mm	
Die thickness	175	μm	

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5 Test conditions

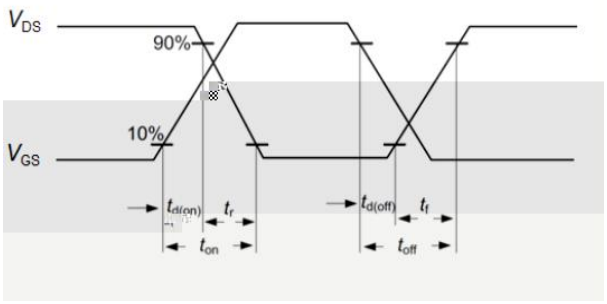


Figure A. Definition of switching times

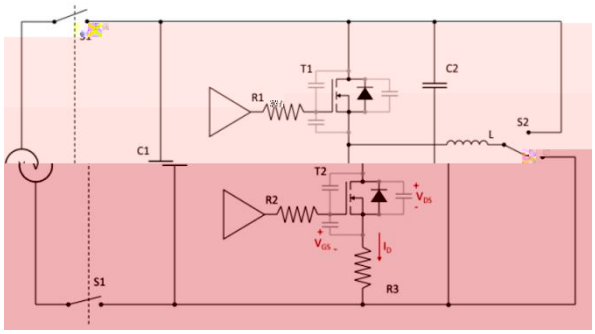


Figure B. Dynamic test cwes

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8. For use of our products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a Sichain representatives, for example but not limited to: transportation equipment,primary communication equipment,traffic lights,fire/crime prevention, safety equipment, medical systems, and power transmission systems.